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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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Complete if Known

Application Number 10/081818

Filing Date February 20, 2002

First Named Inventor Eldridge, Jerome

Group Art Unit 2818

Examiner Name Ho, Tu-Tu

Sheet 1 of 5

Attorney Docket No: 1303.045US1

**US PATENT DOCUMENTS**

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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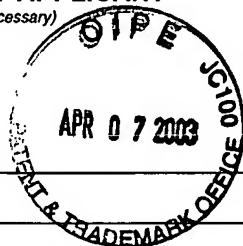
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Sheet 2 of 5

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Application Number	10/081818
Filing Date	February 20, 2002
First Named Inventor	Eldridge, Jerome
Group Art Unit	2818
Examiner Name	Ho, Tu-Tu

Attorney Docket No: 1303.045US1

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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
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Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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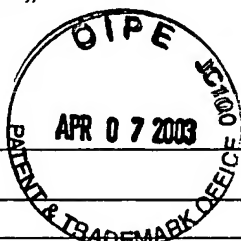
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Sheet 3 of 5

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Application Number	10/081818
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First Named Inventor	Eldridge, Jerome
Group Art Unit	2818
Examiner Name	Ho, Tu-Tu

Attorney Docket No: 1303.045US1

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

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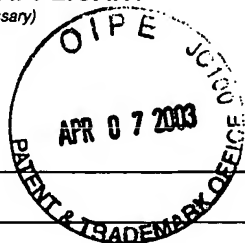
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